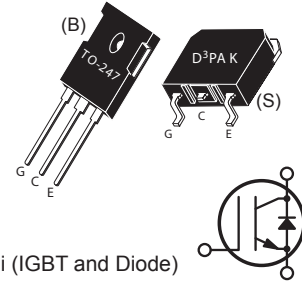



## High Speed PT IGBT

POWER MOS 8® is a high speed Punch-Through switch-mode IGBT. Low  $E_{off}$  is achieved through leading technology silicon design and lifetime control processes. A reduced  $E_{off} - V_{CE(ON)}$  tradeoff results in superior efficiency compared to other IGBT technologies. Low gate charge and a greatly reduced ratio of  $C_{res}/C_{ies}$  provide excellent noise immunity, short delay times and simple gate drive. The intrinsic chip gate resistance and capacitance of the poly-silicone gate structure help control di/dt during switching, resulting in low EMI, even when switching at high frequency.



Combi (IGBT and Diode)

### FEATURES

- Fast switching with low EMI
- Very Low  $E_{off}$  for maximum efficiency
- Ultra low  $C_{res}$  for improved noise immunity
- Low conduction loss
- Low gate charge
- Increased intrinsic gate resistance for low EMI
- RoHS compliant 

### TYPICAL APPLICATIONS

- ZVS phase shifted and other full bridge
- Half bridge
- High power PFC boost
- Welding
- UPS, solar, and other inverters
- High frequency, high efficiency industrial

### Absolute Maximum Ratings

Symbol	Parameter	Ratings	Unit
$V_{CES}$	Collector Emitter Voltage	900	V
$I_{C1}$	Continuous Collector Current @ $T_c = 25^\circ\text{C}$	48	A
$I_{C2}$	Continuous Collector Current @ $T_c = 100^\circ\text{C}$	27	
$I_{CM}$	Pulsed Collector Current <sup>1</sup>	79	
$V_{GE}$	Gate-Emitter Voltage <sup>2</sup>	$\pm 30$	V
$P_D$	Total Power Dissipation @ $T_c = 25^\circ\text{C}$	223	W
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ\text{C}$	79A @ 900V	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Lead Temperature for Soldering: 0.063" from Case for 10 Seconds	300	

### Static Characteristics

 $T_J = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1.0mA$	900			V
$V_{CE(on)}$	Collector-Emitter On Voltage	$V_{GE} = 15V, I_C = 14A$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.5 2.2	3.1	
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	3	4.5	6	
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{CE} = 900V, V_{GE} = 0V$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			350 1500	$\mu\text{A}$
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GS} = \pm 30V$			$\pm 100$	nA

**Dynamic Characteristic**
 **$T_J = 25^\circ\text{C}$  unless otherwise specified**
**APT27GA90BD\_SD15**

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1\text{MHz}$		1390		pF
$C_{oes}$	Output Capacitance			145		
$C_{res}$	Reverse Transfer Capacitance			30		
$Q_g^3$	Total Gate Charge	Gate Charge $V_{GE} = 15V$ $V_{CE} = 450V$ $I_C = 14A$		62		nC
$Q_{ge}$	Gate-Emitter Charge			8		
$Q_{gc}$	Gate- Collector Charge			24		
SSOA	Switching Safe Operating Area	$T_J = 150^\circ\text{C}, R_G = 10\Omega^4, V_{GE} = 15V,$ $L = 100\mu\text{H}, V_{CE} = 900V$	79			A
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 14A$ $R_G = 10\Omega^4$ $T_J = +25^\circ\text{C}$		9		ns
$t_r$	Current Rise Time			8		
$t_{d(off)}$	Turn-Off Delay Time			98		
$t_f$	Current Fall Time			84		
$E_{on2}$	Turn-On Switching Energy			413		
$E_{off}^6$	Turn-Off Switching Energy		287		$\mu\text{J}$	
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 14A$ $R_G = 10\Omega^4$ $T_J = +125^\circ\text{C}$		8		ns
$t_r$	Current Rise Time			10		
$t_{d(off)}$	Turn-Off Delay Time			137		
$t_f$	Current Fall Time			144		
$E_{on2}$	Turn-On Switching Energy			760		
$E_{off}^6$	Turn-Off Switching Energy		647		$\mu\text{J}$	

**Thermal and Mechanical Characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance (IGBT)	-	-	.56	$^\circ\text{C/W}$
$R_{\theta JC}$	Junction to Case Thermal Resistance (Diode)			1.18	
$W_T$	Package Weight	-	5.9	-	g
Torque	Mounting Torque (TO-247 Package), 4-40 or M3 screw			10	in-lbf

1 Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

2 Pulse test: Pulse Width <  $380\mu\text{s}$ , duty cycle < 2%.

3 See Mil-Std-750 Method 3471.

4  $R_G$  is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

5  $E_{on2}$  is the clamped inductive turn on energy that includes a commutating diode reverse recovery current in the IGBT turn on energy loss. A combi device is used for the clamping diode.

6  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1.

**Microsemi reserves the right to change, without notice, the specifications and information contained herein.**

Typical Performance Curves

APT27GA90BD\_SD15

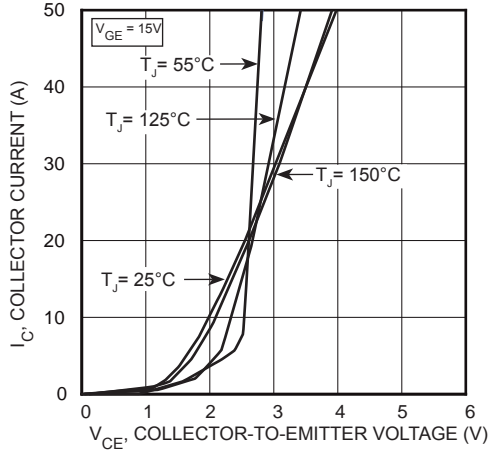


FIGURE 1, Output Characteristics ( $T_J = 25^\circ C$ )

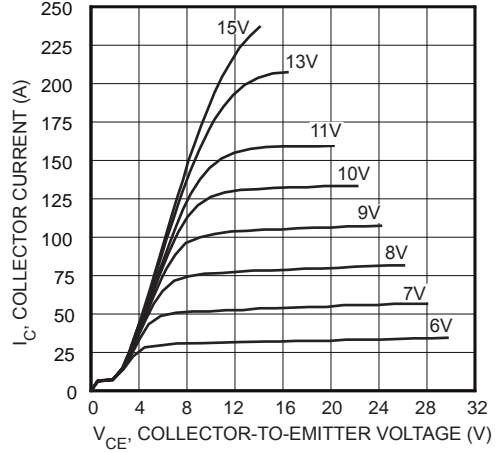


FIGURE 2, Output Characteristics ( $T_J = 25^\circ C$ )

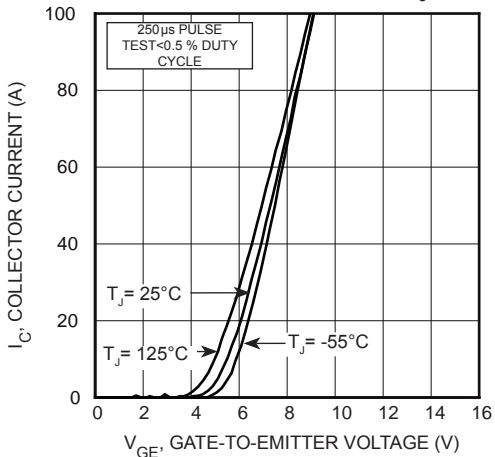


FIGURE 3, Transfer Characteristics

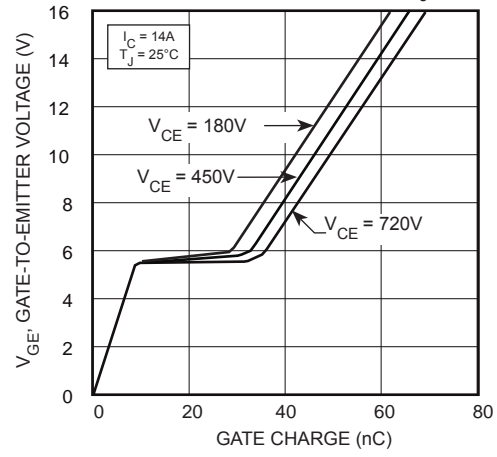


FIGURE 4, Gate charge

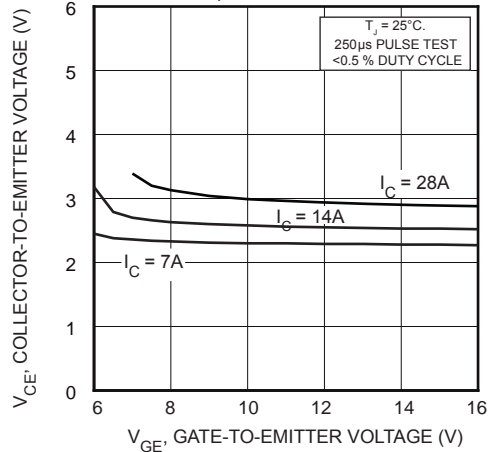


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

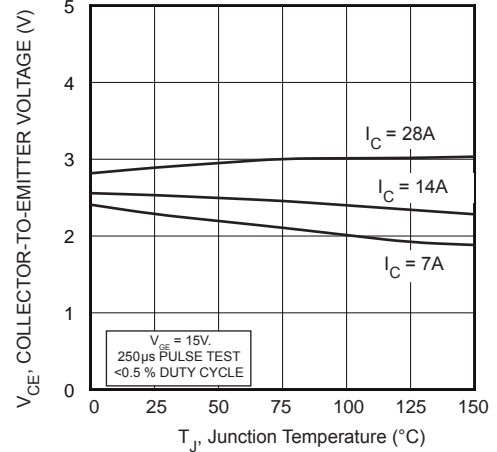


FIGURE 6, On State Voltage vs Junction Temperature

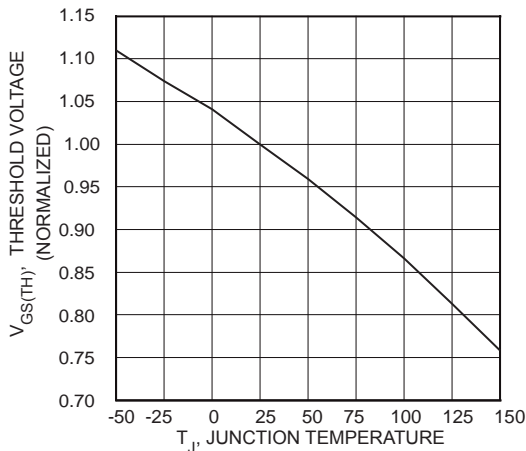


FIGURE 7, Threshold Voltage vs Junction Temperature

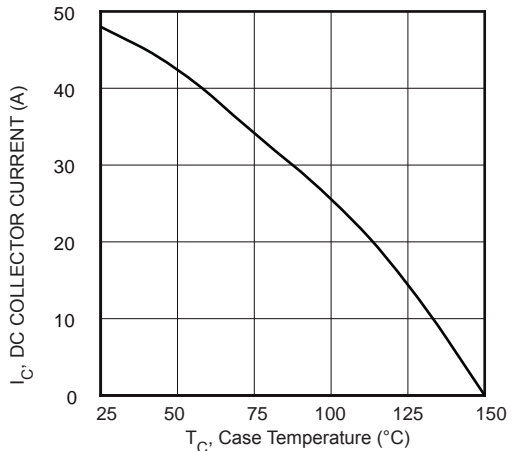


FIGURE 8, DC Collector Current vs Case Temperature

# Typical Performance Curves

APT27GA90BD\_SD15

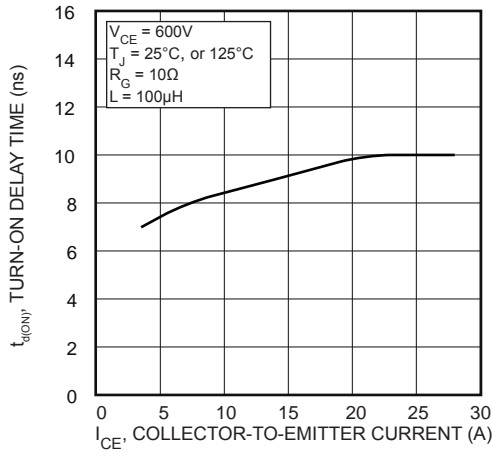


FIGURE 9, Turn-On Delay Time vs Collector Current

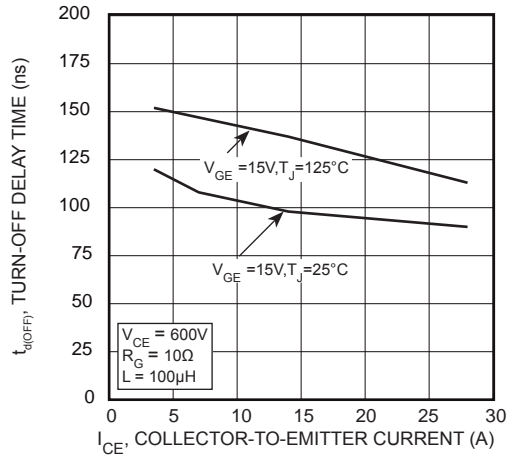


FIGURE 10, Turn-Off Delay Time vs Collector Current

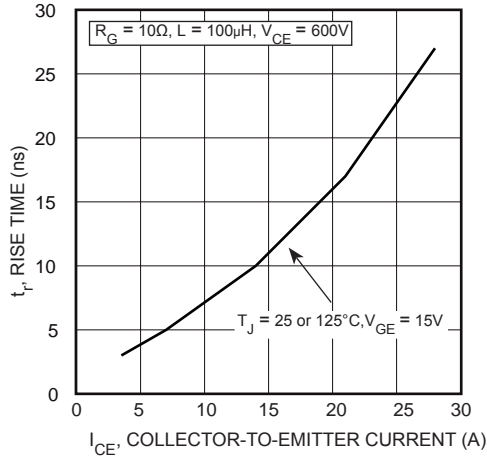


FIGURE 11, Current Rise Time vs Collector Current

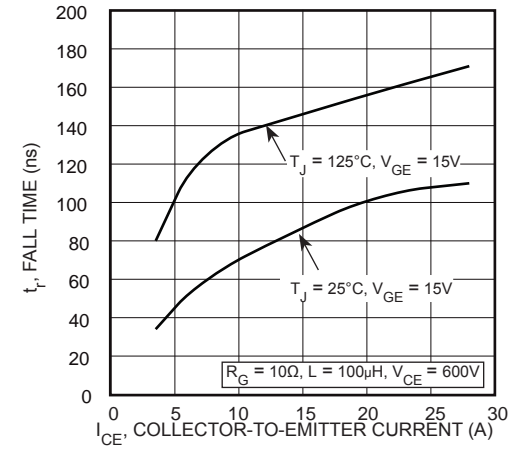


FIGURE 12, Current Fall Time vs Collector Current

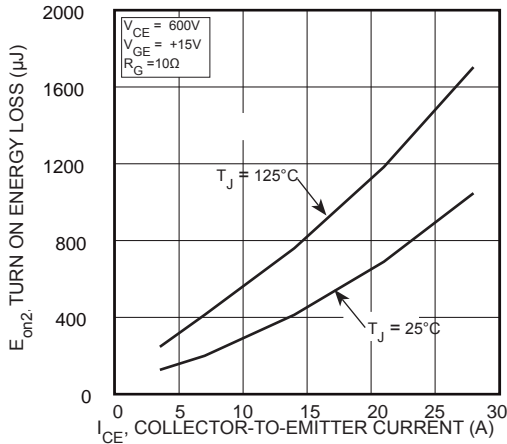


FIGURE 13, Turn-On Energy Loss vs Collector Current

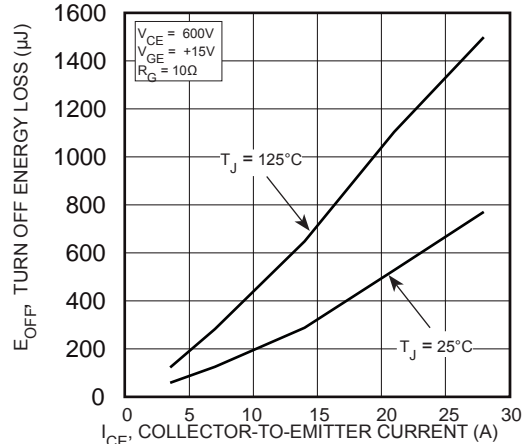


FIGURE 14, Turn-Off Energy Loss vs Collector Current

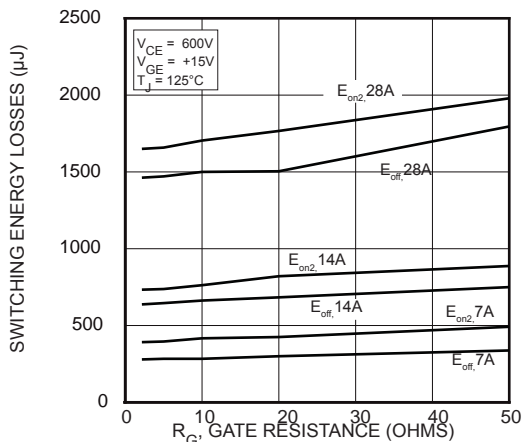


FIGURE 15, Switching Energy Losses vs Gate Resistance

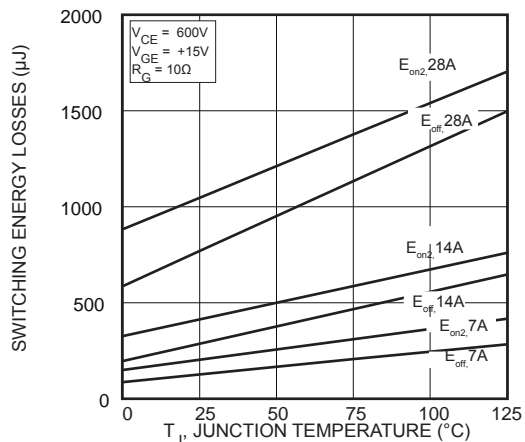


FIGURE 16, Switching Energy Losses vs Junction Temperature

Typical Performance Curves

APT27GA90BD\_SD15

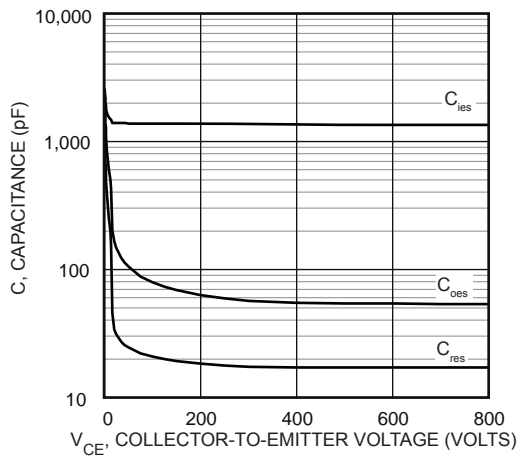


FIGURE 17, Capacitance vs Collector-To-Emitter Voltage

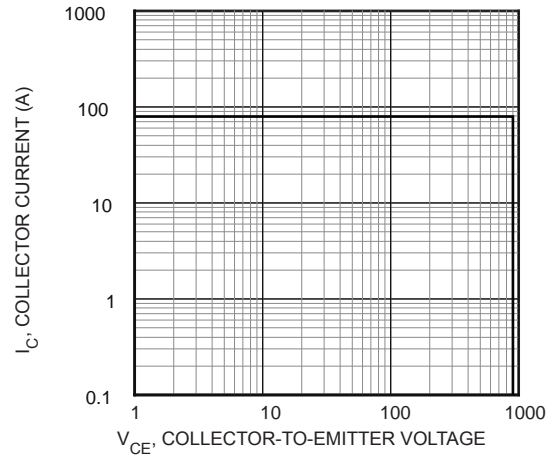


FIGURE 18, Minimum Switching Safe Operating Area

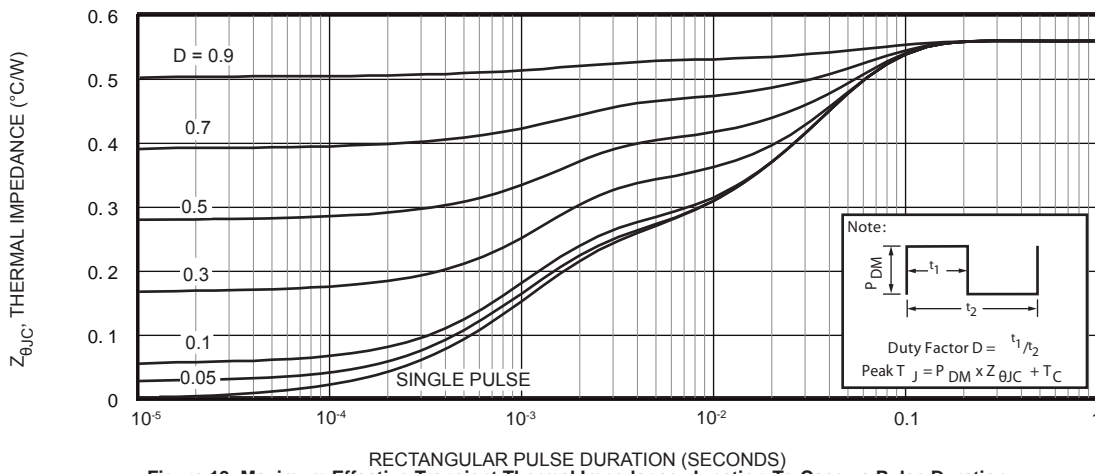


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

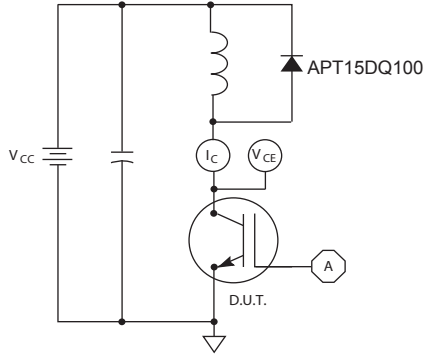


Figure 20, Inductive Switching Test Circuit

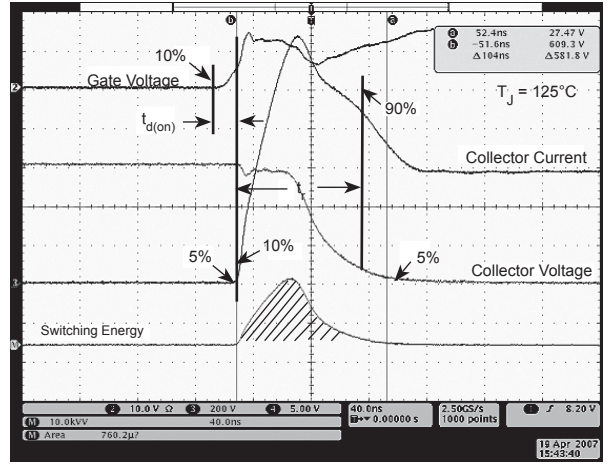


Figure 21, Turn-on Switching Waveforms and Definitions

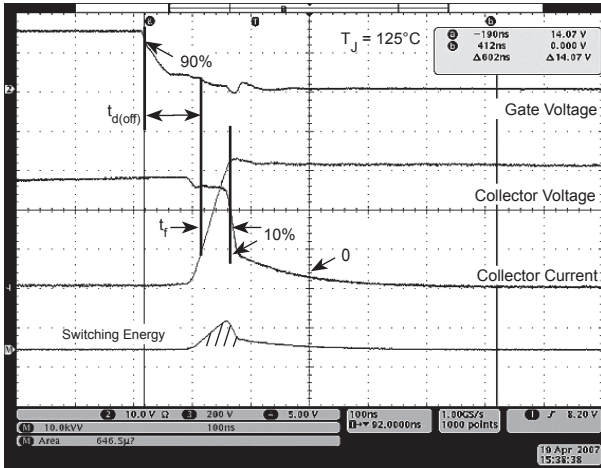


Figure 22, Turn-off Switching Waveforms and Definitions

# ULTRAFAST SOFT RECOVERY RECTIFIER DIODE

## MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT27GA90BD_SD15	Unit
$I_{F(AV)}$	Maximum Average Forward Current ( $T_C = 126^\circ\text{C}$ , Duty Cycle = 0.5)	15	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	29	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3 ms)	80	

## STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Type	Max	Unit
$V_F$	Forward Voltage		$I_F = 15\text{A}$	2.5	Volts
			$I_F = 30\text{A}$	3.06	
			$I_F = 15\text{A}, T_J = 125^\circ\text{C}$	1.92	

## DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$t_{rr}$	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	20	-	ns
$t_{rr}$	Reverse Recovery Time	$I_F = 15\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 25^\circ\text{C}$	-	235	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	185	-	
$I_{RRM}$	Maximum Reverse Recovery Current		-	3	-	
$t_{rr}$	Reverse Recovery Time	$I_F = 15\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 125^\circ\text{C}$	-	300	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	810	-	nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	6	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 15\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 125^\circ\text{C}$	-	125	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	1150	-	nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	19	-	Amps

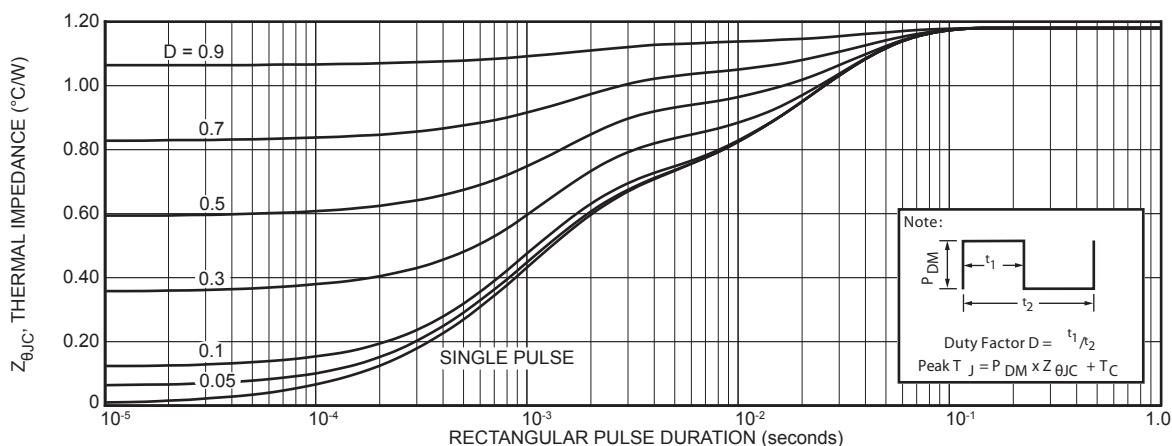


FIGURE 23. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

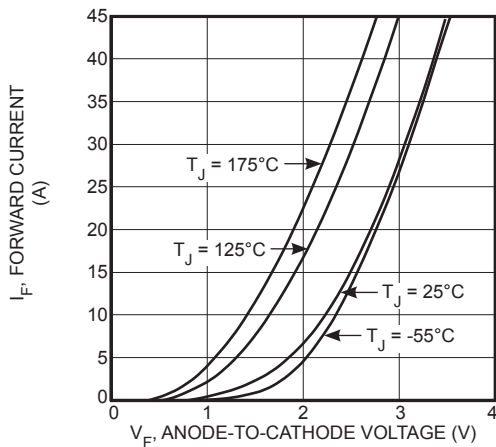


Figure 24. Forward Current vs. Forward Voltage

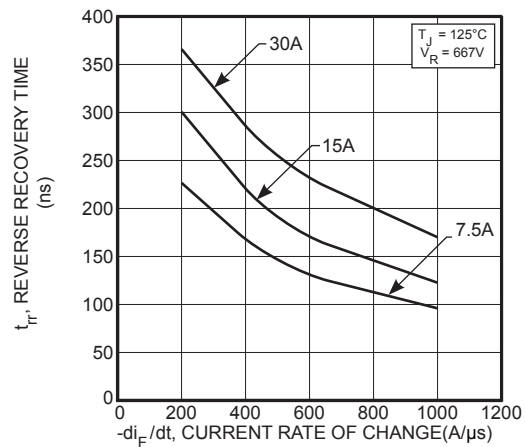


Figure 25. Reverse Recovery Time vs. Current Rate of Change

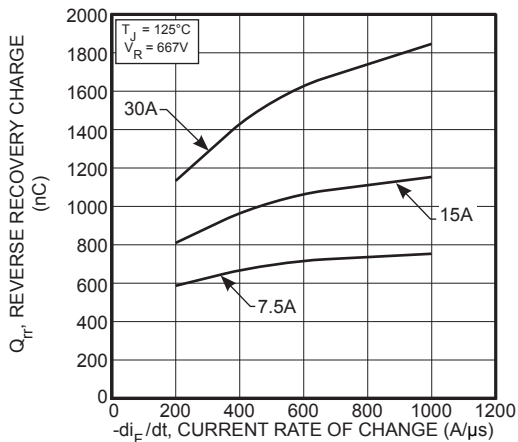


Figure 26. Reverse Recovery Charge vs. Current Rate of Change

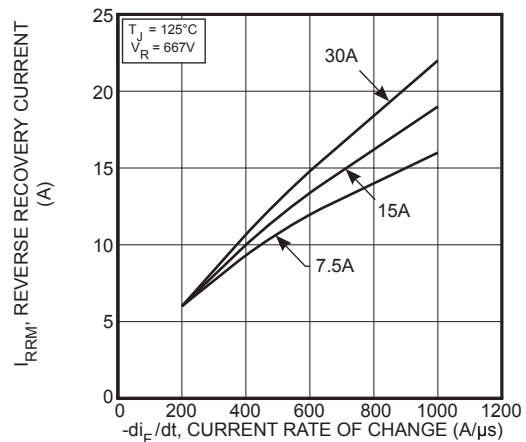


Figure 27. Reverse Recovery Current vs. Current Rate of Change

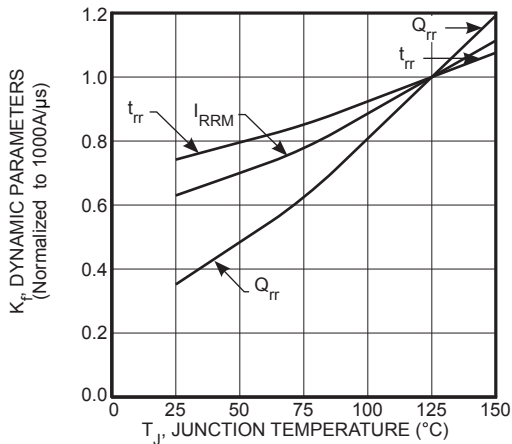


Figure 28. Dynamic Parameters vs. Junction Temperature

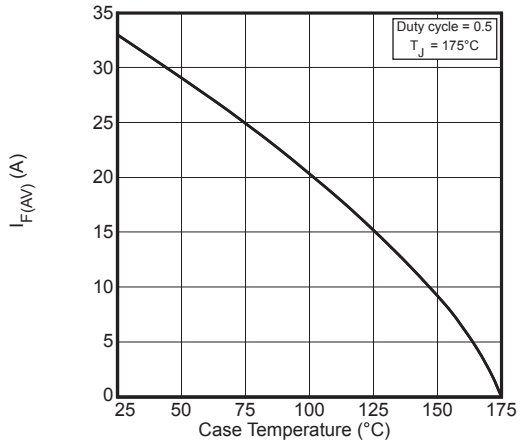


Figure 29. Maximum Average Forward Current vs. Case Temperature

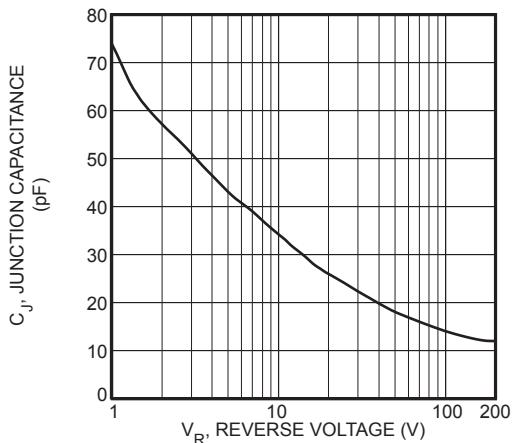


Figure 30. Junction Capacitance vs. Reverse Voltage



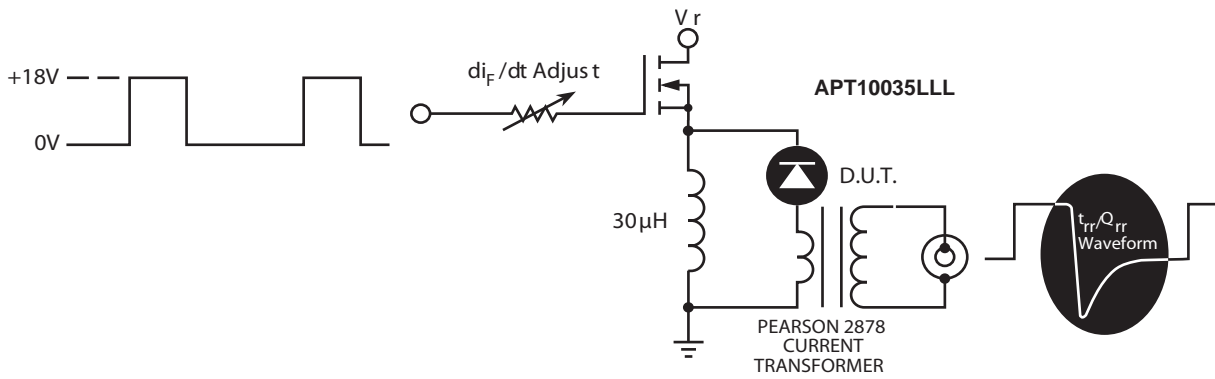


Figure 31. Diode Test Circuit

- 1 I<sub>F</sub> - Forward Conduction Current
- 2 di<sub>F</sub>/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I<sub>RRM</sub> - Maximum Reverse Recovery Current
- 4 t<sub>rr</sub> - Reverse Recovery Time measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I<sub>RRM</sub> and 0.25 I<sub>RRM</sub> passes through zero.
- 5 Q<sub>rr</sub> - Area Under the Curve Defined by I<sub>RRM</sub> and t<sub>rr</sub>.

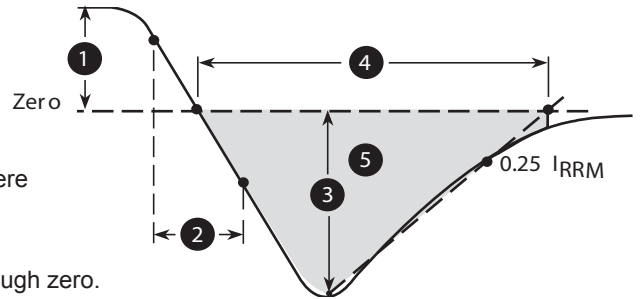
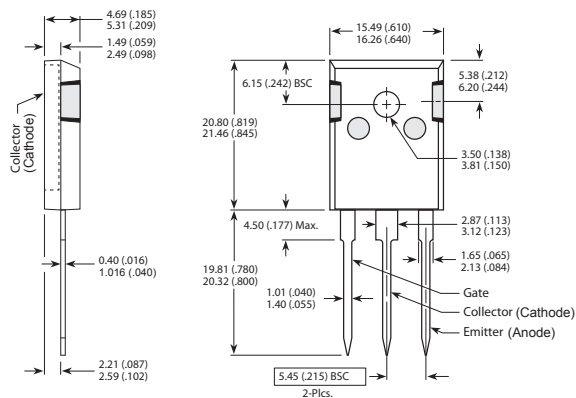


Figure 32. Diode Reverse Recovery Waveform Definition

**TO-247 Package Outline**

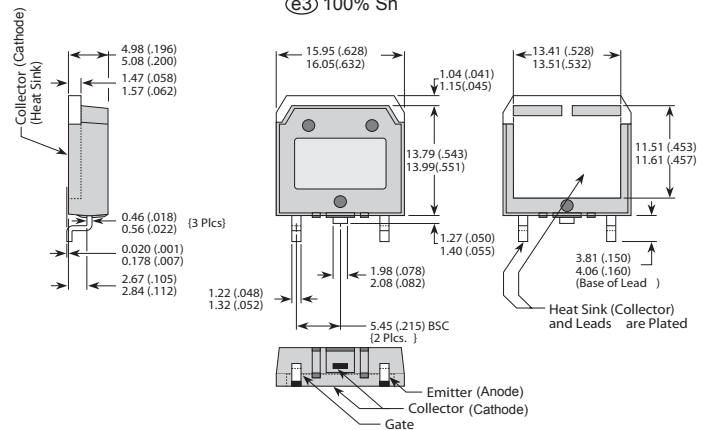
Ⓔ1 SAC: Tin, Silver, Copper



Dimensions in Millimeters (Inches)

**D<sup>3</sup>PAK Package Outline**

Ⓔ3 100% Sn



Dimensions in Millimeters (Inches)

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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